

INCHANGE Semiconductor

isc Product Specification

isc Silicon NPN Darlington Power Transistor

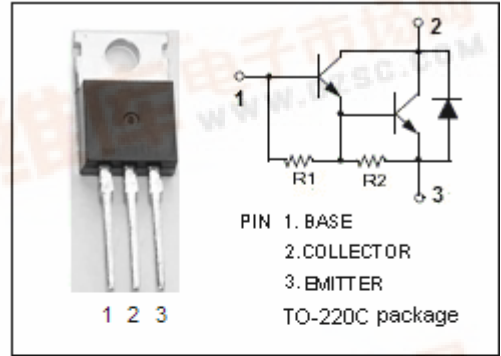
BU910

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 350V(\text{Min})$
- High Switching Speed

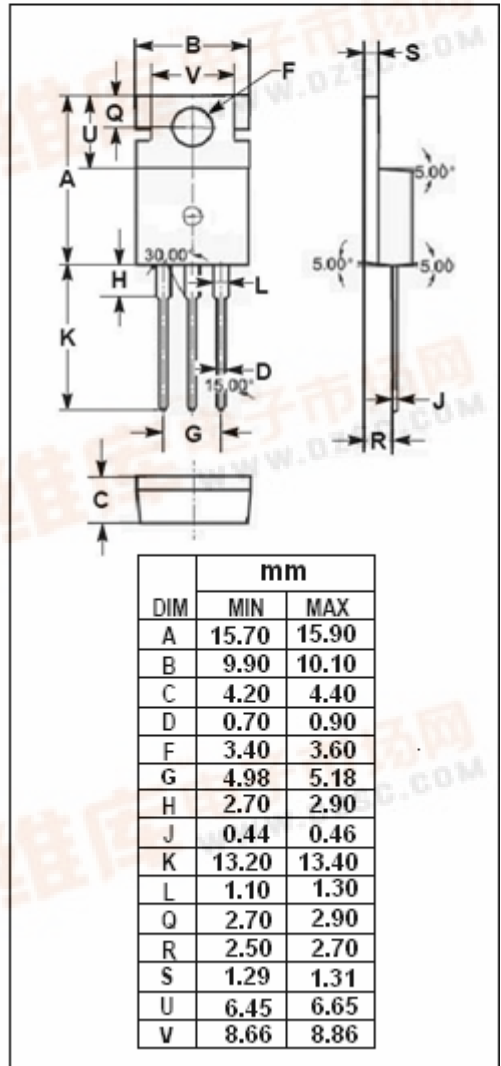
APPLICATIONS

- Designed for applications such as electronic ignition, DC and AC motor controls, solenoid drivers, etc.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	350	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	6	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current	1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.08	$^\circ\text{C/W}$



isc Silicon NPN Darlington Power Transistor**BU910****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE0(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	350			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=50\text{mA}$			1.8	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.2\text{A}$			1.8	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=50\text{mA}$			2.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.2\text{A}$			2.5	V
I_{CES}	Collector Cutoff Current	$V_{CE}=400\text{V}; V_{BE}=0$ $V_{CE}=400\text{V}; V_{BE}=0, T_C=125^\circ\text{C}$			1 5	mA
I_{CEO}	Collector Cutoff Current	$V_{CE}=350\text{V}; I_B=0$			1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			5	mA
V_{ECF}	C-E Diode Forward Voltage	$I_F=4\text{A}$			2.5	V